

N-CHANNEL LATERAL POWER MOSFET FOR AUDIO

ALF08N16K/ALF08N20K

- Designed specifically for linear audio amplifier applications
- High-speed for high bandwidth amplifiers
- High voltage rating – 160V & 200V
- TO-3 metal package
- Enhanced oscillation suppression in multi-device applications
- Complimentary P-channel available – ALF08P16K/ALF08P20K



ABSOLUTE MAXIMUM RATINGS

($T_C = 25^\circ\text{C}$ unless otherwise stated)

		ALF08N16K	ALF08N20K
V_{DSS}	Drain - Source Voltage	160V	200V
V_{GSS}	Gate - Source Voltage	±20V	
I_D	Continuous Drain Current	8A	
I_{DR}	Body Drain Diode Current	8A	
P_D	Allowable Power Dissipation $T_{case} = 25^\circ\text{C}$	125W	
T_{ch}	Channel Temperature	150°C	
T_{stg}	Storage Temperature Range	-55 to +150°C	

THERMAL PROPERTIES

Symbols	Parameters	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction To Case			1	°C/W

Magnatec reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Magnatec is believed to be both accurate and reliable at the time of going to press. However Magnatec assumes no responsibility for any errors or omissions discovered in its use. Magnatec encourages customers to verify that datasheets are current before placing orders.

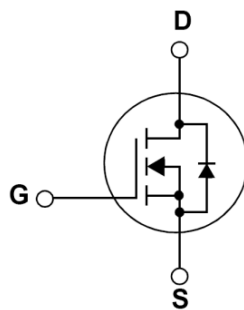
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
BV _{DSX}	Drain-Source Breakdown Voltage	V _{GS} = -10V	ALF08N16K	160		V
		I _D = 10mA	ALF08N20K	200		
I _{GSS}	Gate-Source Leakage Current	V _{DS} = 0 V _{GS} = ±20V			100	μA
V _{GS(off)}	Gate-Source Cut-off Voltage	V _{DS} = 10V I _D = 100mA	0.15		1.5	V
V _{DS(sat)*}	Drain-Source Saturation Voltage	V _{GD} = 0 I _D = 8A			12	V
y _{fs} *	Forward Transfer Admittance	V _{DS} = 10V I _{DS} = 3A	0.7		2	S(Ω)
I _{DSX}	Drain-Source Cut-Off Current	V _{GS} = -10V	V _{DS} = 160V		10	mA
			V _{DS} = 200V		10	

* Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2%

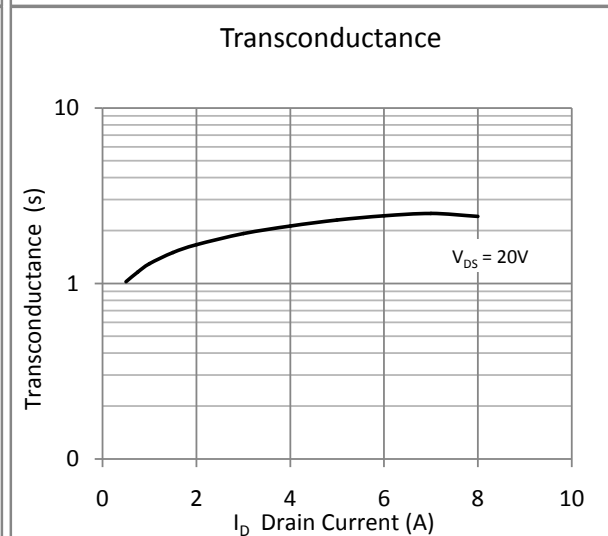
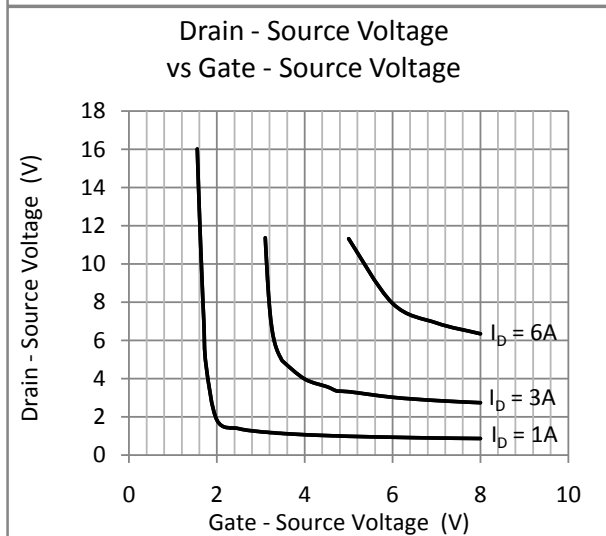
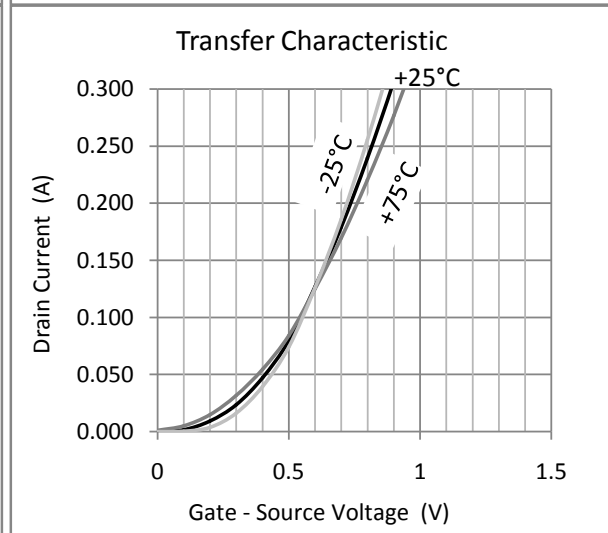
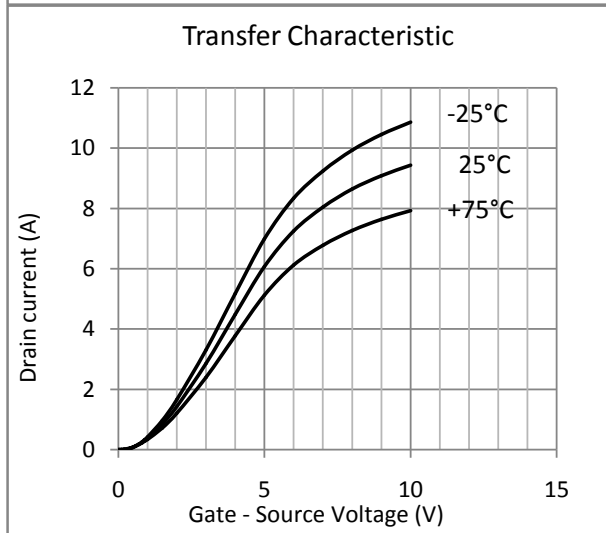
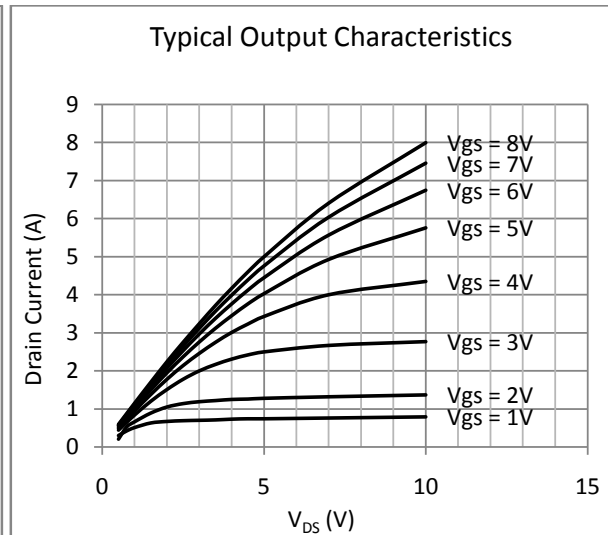
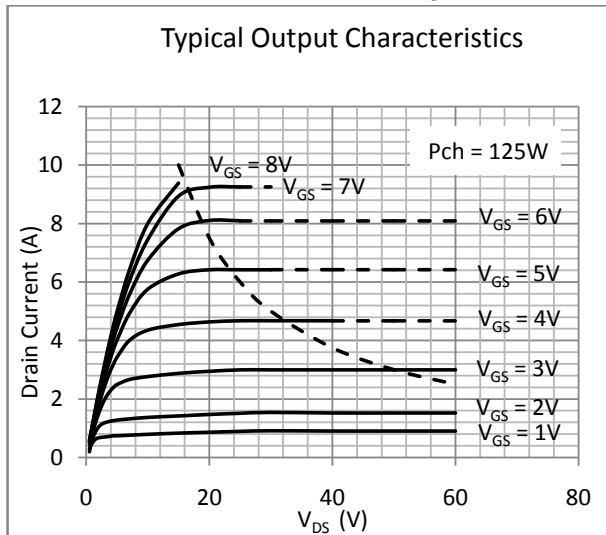
DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{GS} = 0		500		pF
C _{oss}	Output Capacitance	V _{DS} = 10V		300		
C _{rss}	Reverse Transfer Capacitance	f = 1.0MHz		10		
t _{on}	Turn-On Time	V _{DS} = 20V		100		ns
t _{off}	Turn-Off Time	I _D = 5A		50		

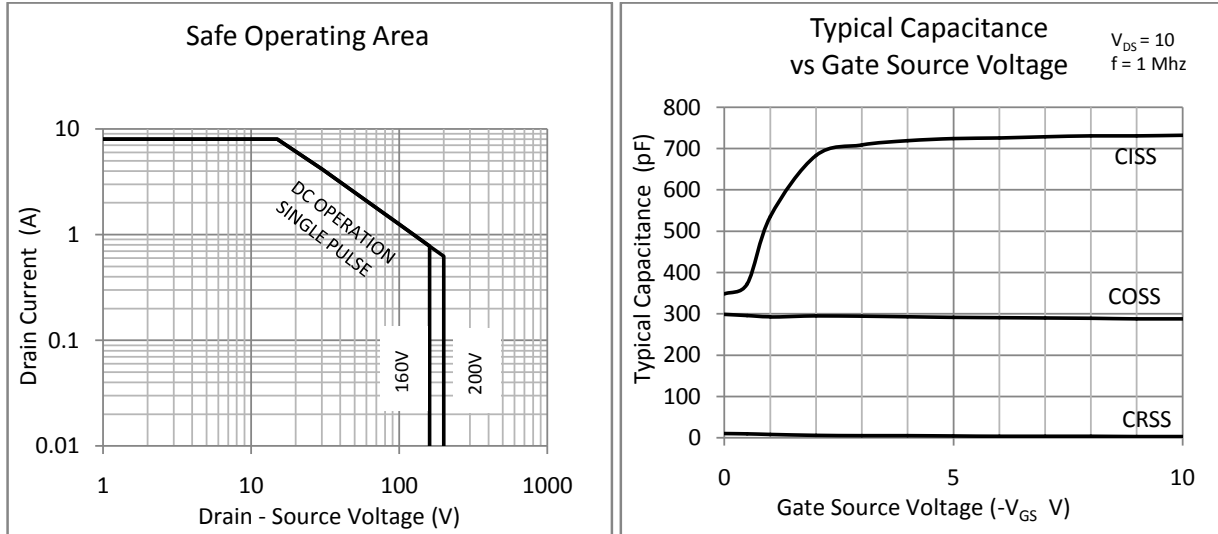


Please Note: These lateral mosfets do not include a G-S protection network and care must therefore be taken with static handling precautions and the appropriate protection in the amplifier circuit. Please refer to the application notes for more information.

GENERAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

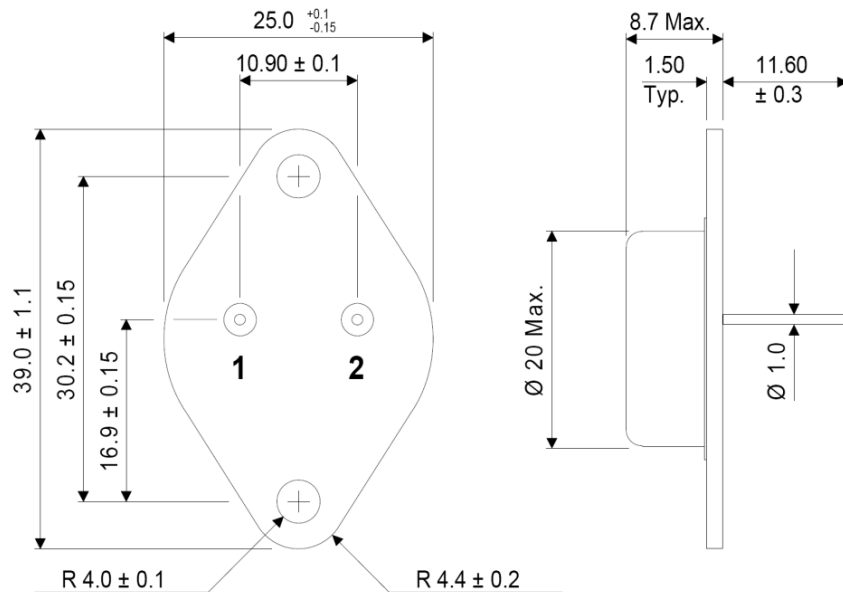


GENERAL CHARACTERISTICS CONTINUED ($T_C = 25^\circ\text{C}$ unless otherwise stated)



MECHANICAL DATA

Dimensions in mm



TO-3

Pin 1 – Gate

Pin 2 – Drain

Case – Source